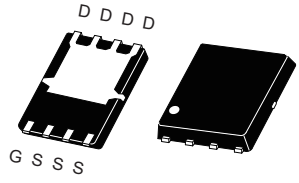
CEZ1320AP

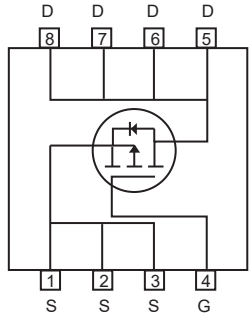
P-Channel Enhancement Mode Field Effect Transistor

FEATURES

- -200V, -12.5A, $R_{DS(ON)}$= 275 mΩ @V_{GS} = -10V.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- Pb-free lead plating ; RoHS compliant.
- Halogen Free.
- Surface mount Package.



P-PAK 5X6



Applications

- Switched mode power supplies.
- Lighting.
- DC Motor control.
- Load switch.
- battery powered.

ABSOLUTE MAXIMUM RATINGS T_C = 25°C unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-200	V
Gate-Source Voltage	V_{GS}	±30	V
Drain Current-Continuous	I_D @$R_{\theta JC}$	-12.5	A
Drain Current-Continuous	I_D @$R_{\theta JA}$	-3.6	A
Drain Current-Pulsed [a]	I_{DM} @$R_{\theta JC}$	-50	A
Drain Current-Pulsed [a]	I_{DM} @$R_{\theta JA}$	-14.4	A
Maximum Power Dissipation	P_D	73.5	W
Operating and Store Temperature Range	T_J,T_{stg}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.7	°C/W
Thermal Resistance, Junction-to-Ambient [b]	$R_{\theta JA}$	20	°C/W

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = -250μA	-200			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -200V, V_{GS} = 0V			-1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	V_{GS} = 30V, V_{DS} = 0V			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	V_{GS} = -30V, V_{DS} = 0V			-100	nA
On Characteristics [c]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = -250μA	-2		-4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D =-5.2A		220	275	mΩ
Dynamic Characteristics [d]						
Input Capacitance	C_{iss}	V_{DS} = -25V, V_{GS} = 0V, f = 1.0 MHz		3790		pF
Output Capacitance	C_{oss}			145		pF
Reverse Transfer Capacitance	C_{rss}			105		pF
Switching Characteristics [d]						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -100V, I_D = -6A, V_{GS} = -10V, R_{GEN} = 25Ω		41		ns
Turn-On Rise Time	t_r			38		ns
Turn-Off Delay Time	$t_{d(off)}$			191		ns
Turn-Off Fall Time	t_f			71		ns
Total Gate Charge	Q_g	V_{DD} = -160V, I_D = -6A, V_{GS} = -10V		65		nC
Gate-Source Charge	Q_{gs}			10		nC
Gate-Drain Charge	Q_{gd}			21		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Forward Current	I_S				-12.5	A
Drain-Source Diode Forward Voltage [c]	V_{SD}	V_{GS} = 0V, I_S = -10.5A			-1.2	V

Notes :
a.Repetitive Rating : Pulse width limited by maximum junction temperature.
b.Surface Mounted on FR4 Board, t ≤ 10 sec.
c.Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
d.Guaranteed by design, not subject to production testing.
e.L =3mH, I_{AS} =11.5A, V_{DD} = 25V, R_G = 25Ω, Starting $T_J = 25^{\circ}C$.

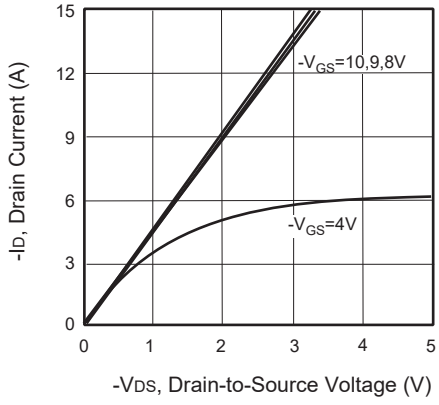


Figure 1. Output Characteristics

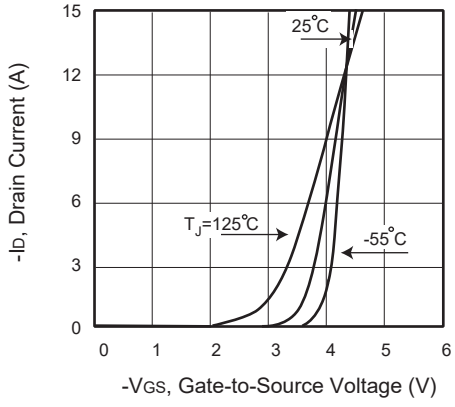


Figure 2. Transfer Characteristics

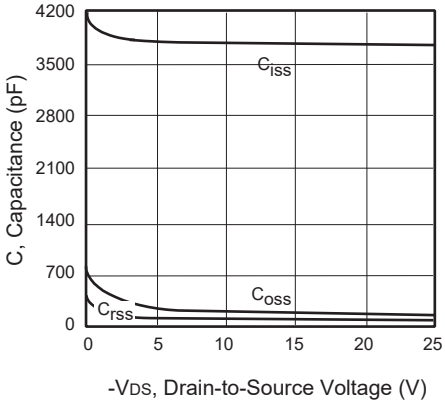


Figure 3. Capacitance

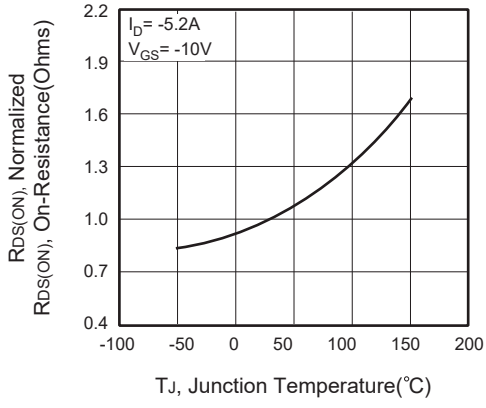


Figure 4. On-Resistance Variation with Temperature

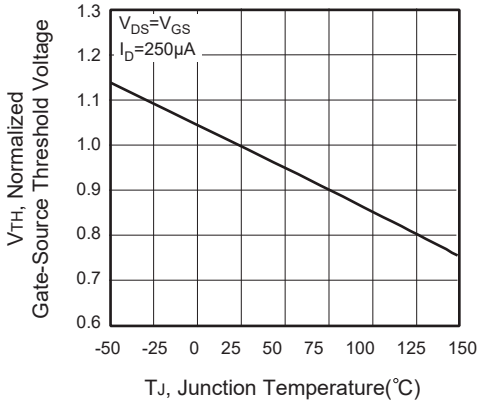


Figure 5. Gate Threshold Variation with Temperature

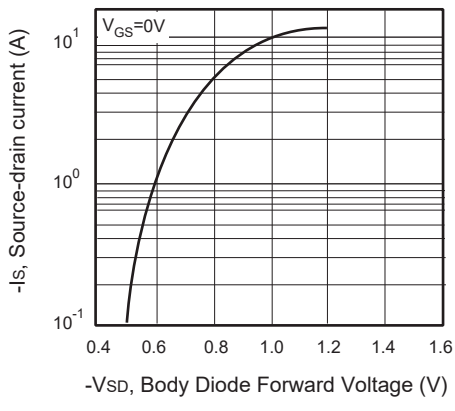


Figure 6. Body Diode Forward Voltage Variation with Source Current

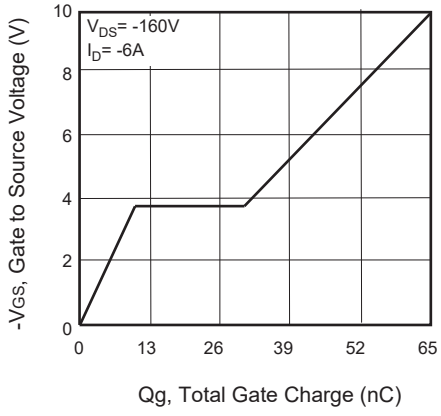


Figure 7. Gate Charge

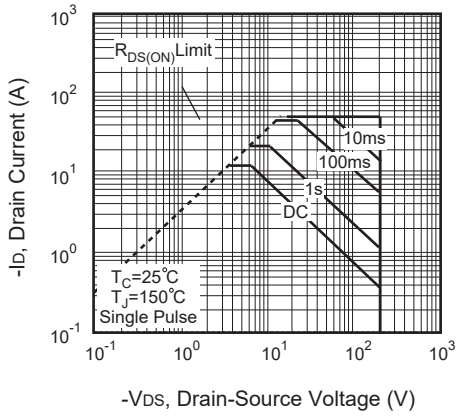


Figure 8. Maximum Safe Operating Area

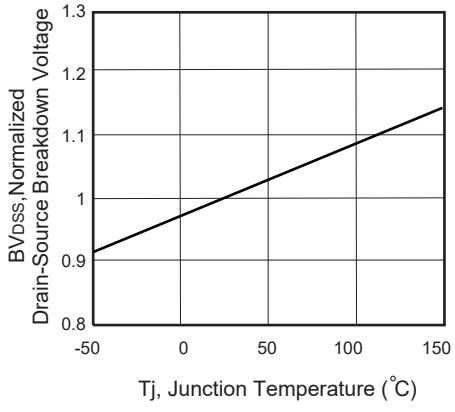


Figure 9. Breakdown Voltage Variation VS Temperature

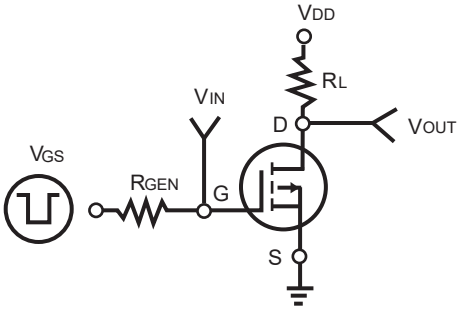


Figure 10. Switching Test Circuit

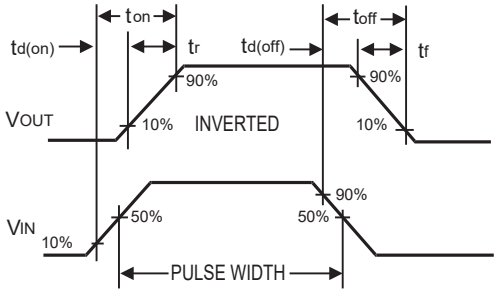


Figure 11. Switching Waveforms

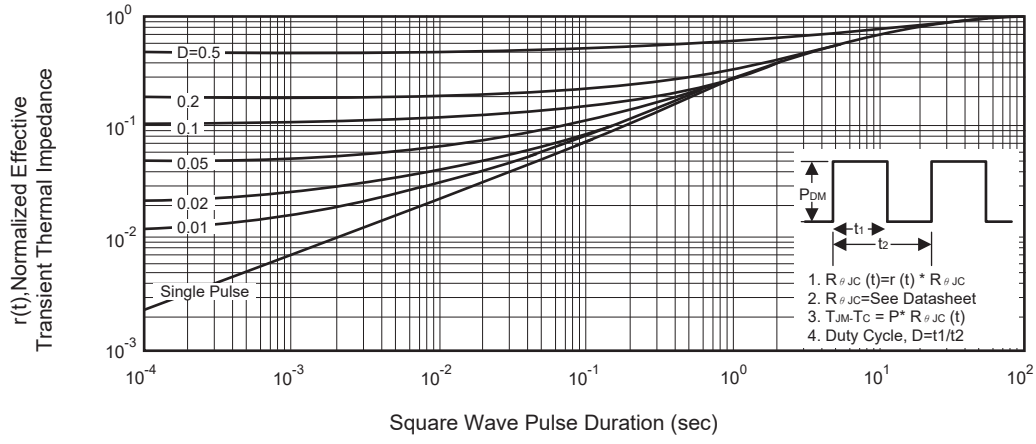
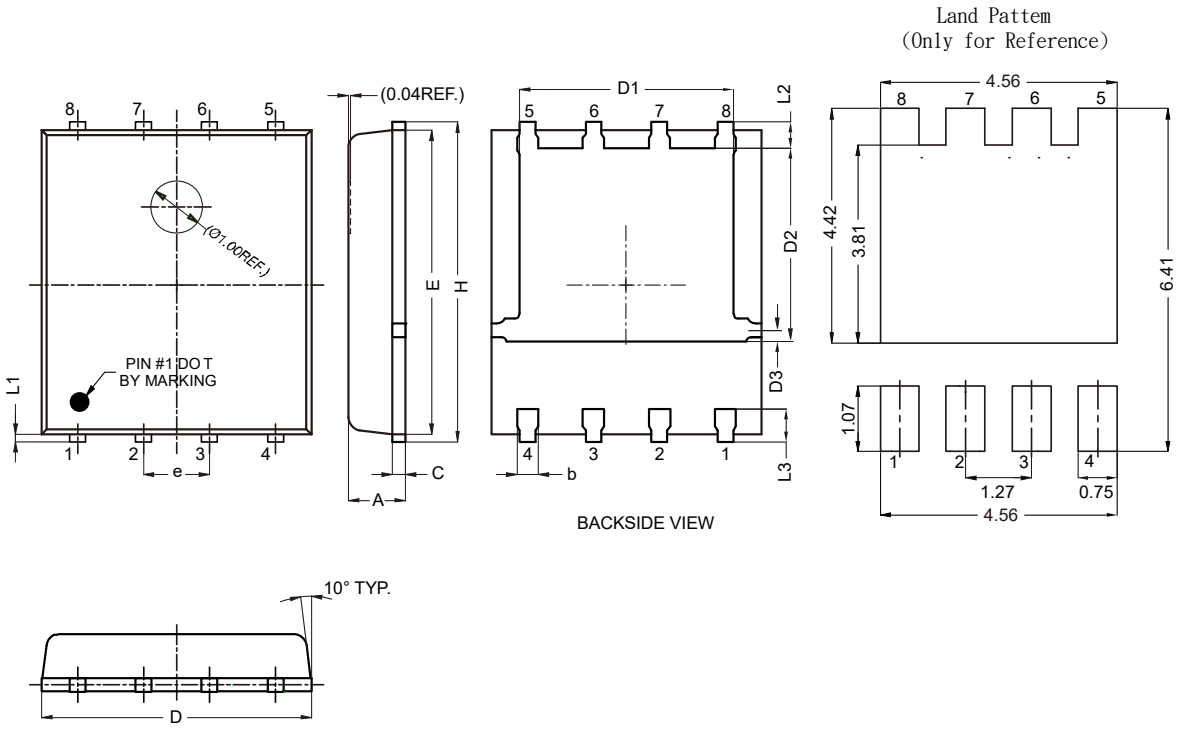


Figure 11. Normalized Thermal Transient Impedance Curve

P-PAK5X6 產品外觀尺寸圖 (Product Outline Dimension)

SINGLE PAD 尺寸圖



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.000	1.200	0.039	0.047
b	0.330	0.500	0.013	0.020
c	0.200	0.300	0.008	0.012
D	5.000	5.400	0.197	0.213
D1	3.800	4.250	0.150	0.167
D2	3.520	3.920	0.139	0.154
D3	0.396	0.436	0.016	0.017
E	5.760	5.960	0.227	0.235
e	1.270 TYP		0.050 TYP	
H	6.000	6.300	0.236	0.248
L1	0.080	0.220	0.003	0.009
L2	0.400	0.600	0.016	0.024
L3	0.500	0.700	0.020	0.028